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Kind regards,

Team Nexperia

74HC390; 74HCT390

Dual decade ripple counter

Rev. 3 — 16 August 2016

Product data sheet

1. General description

The 74HC390; 74HCT390 is a dual 4-bit decade ripple counter divided into four separately clocked sections. The counters have two divide-by-2 sections and two divide-by-5 sections. These sections share an asynchronous master reset input ($\overline{\text{nMR}}$) and can be used in a BCD decade or bi-quinary configuration. If master reset inputs $\overline{1\text{MR}}$ and $\overline{2\text{MR}}$ are used to clear all 8 bits of the counter simultaneously, numerous counting configurations are possible within one package. Section clocks $\overline{\text{nCP0}}$ and $\overline{\text{nCP1}}$, allow ripple counter or frequency division applications of divide-by-2, 4, 5, 10, 20, 25, 50 or 100. The HIGH-to-LOW transition of the clock inputs $\overline{\text{nCP0}}$ and $\overline{\text{nCP1}}$ trigger each section. For BCD decade operation, the nQ0 output is connected to the $\overline{\text{nCP1}}$ input of the divide-by-5 section. For bi-quinary decade operation, the nQ3 output is connected to the $\overline{\text{nCP0}}$ input and nQ0 becomes the decade output. A HIGH on the $\overline{\text{nMR}}$ input overrides the clocks and sets the four outputs LOW. Inputs include clamp diodes. It enables the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

2. Features and benefits

- Input levels:
 - ◆ For 74HC390: CMOS level
 - ◆ For 74HCT390: TTL level
- Two BCD decade or bi-quinary counters
- One device can be configured to divide-by-2, 4, 5, 10, 20, 25, 50 or 100
- Two master reset inputs to clear each decade counter individually
- Specified in compliance with JEDEC standard no. 7A
- ESD protection:
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V
- Multiple package options
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$



3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC390D	−40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74HCT390D				
74HC390DB	−40 °C to +125 °C	SSOP16	plastic shrink small outline package; 16 leads; body width 5.3 mm	SOT338-1
74HCT390DB				
74HCT390PW	−40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1

4. Functional diagram

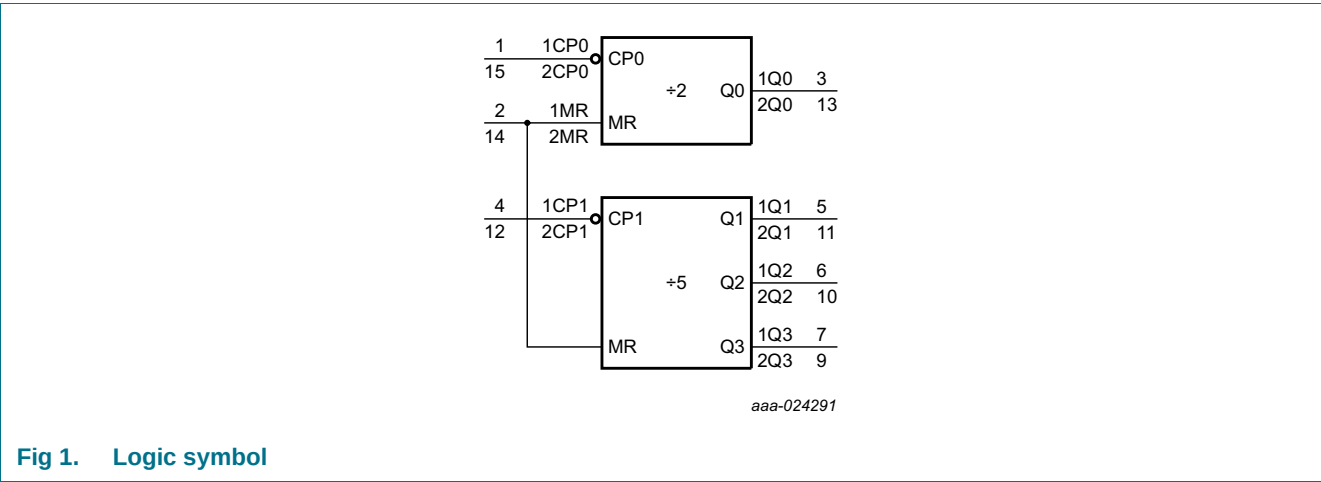


Fig 1. Logic symbol

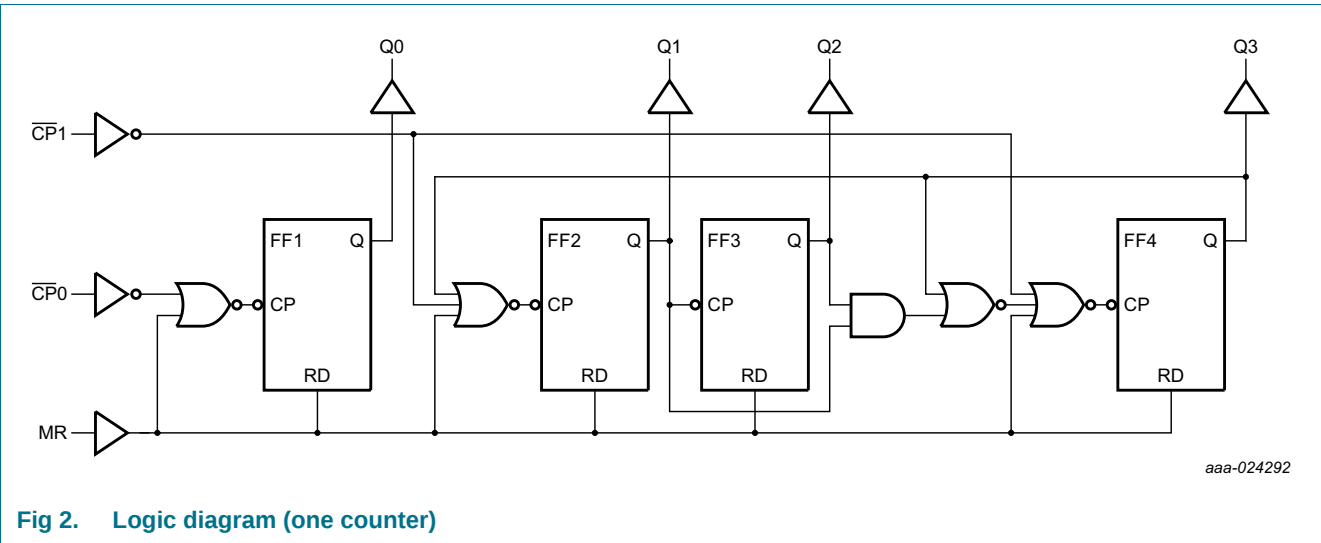


Fig 2. Logic diagram (one counter)

5. Pinning information

5.1 Pinning

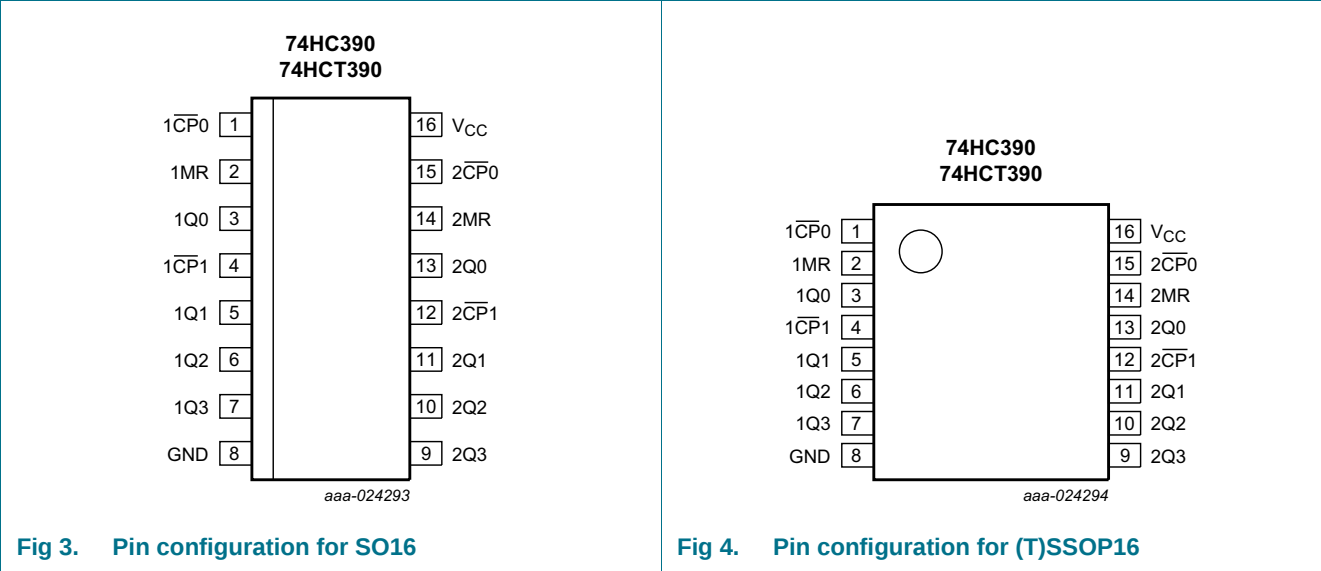


Fig 3. Pin configuration for SO16

Fig 4. Pin configuration for (T)SSOP16

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
1CP0, 2CP0	1, 15	clock input divide-by-2 section (HIGH-to-LOW; edge-triggered)
1MR, 2MR	2, 14	asynchronous master reset input (active HIGH)
1Q0, 1Q1, 1Q2, 1Q3	3, 5, 6, 7	flip-flop outputs
1CP1, 2CP1	4, 12	clock input divide-by-5 section (HIGH-to-LOW; edge-triggered)
GND	8	ground (0 V)
2Q0, 2Q1, 2Q2, 2Q3	13, 11, 10, 9	flip-flop outputs
VCC	16	supply voltage

6. Functional description

Table 3. BCD count sequence^[1]

Count	Output			
	nQ0	nQ1	nQ2	nQ3
0	L	L	L	L
1	H	L	L	L
2	L	H	L	L
3	H	H	L	L
4	L	L	H	L
5	H	L	H	L
6	L	H	H	L
7	H	H	H	L
8	L	L	L	H
9	H	L	L	H

[1] Output nQ0 connected to $\overline{\text{nCP1}}$; counter input on $\overline{\text{nCP0}}$.

H = HIGH voltage level

L = LOW voltage level

Table 4. Bi-quinary count sequence^[1]

Count	Output			
	nQ0	nQ1	nQ2	nQ3
0	L	L	L	L
1	L	H	L	L
2	L	L	H	L
3	L	H	H	L
4	L	L	L	H
5	H	L	L	L
6	H	H	L	L
7	H	L	H	L
8	H	H	H	L
9	H	L	L	H

[1] Output nQ3 connected to $\overline{\text{nCP0}}$; counter input on $\overline{\text{nCP1}}$.

H = HIGH voltage level

L = LOW voltage level

7. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	-	± 20	mA
I_O	output current	$-0.5\text{ V} < V_O < V_{CC} + 0.5\text{ V}$	-	± 25	mA
I_{CC}	supply current		-	+50	mA
I_{GND}	ground current		-50	-	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	SO16 and (T)SSOP16 packages [1]	-	500	mW

- [1] For SO16 packages: above 70 °C, the value of P_{tot} derates linearly with 8 mW/K.
For (T)SSOP16 packages: above 60 °C, the value of P_{tot} derates linearly with 5.5 mW/K.

8. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V)

Symbol	Parameter	Conditions	74HC390			74HCT390			Unit
			Min	Typ	Max	Min	Typ	Max	
V_{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	$V_{CC} = 2.0\text{ V}$	-	-	625	-	-	-	ns/V
		$V_{CC} = 4.5\text{ V}$	-	1.67	139	-	1.67	139	ns/V
		$V_{CC} = 6.0\text{ V}$	-	-	83	-	-	-	ns/V

9. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
74HC390										
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V

Table 7. Static characteristics ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = –20 µA; V _{CC} = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I _O = –20 µA; V _{CC} = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –20 µA; V _{CC} = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I _O = –4.0 mA; V _{CC} = 4.5 V	3.98	4.32	-	3.84	-	3.7	-	V
		I _O = –5.2 mA; V _{CC} = 6.0 V	5.48	5.81	-	5.34	-	5.2	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}								
		I _O = 20 µA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 20 µA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1	-	±1	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	8.0	-	80	-	160	µA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF
74HCT390										
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	-	0.8	V
V _{OH}	HIGH-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = –20 µA	4.4	4.5	-	4.4	-	4.4	-	V
		I _O = –4.0 mA	3.98	4.32	-	3.84	-	3.7	-	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V								
		I _O = 20 µA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 5.5 V	-	0.15	0.26	-	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±0.1	-	±1	-	±1	µA
I _{CC}	supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 5.5 V	-	-	8.0	-	80	-	160	µA
ΔI _{CC}	additional supply current	per input pin; V _I = V _{CC} – 2.1 V; other inputs at V _{CC} or GND; V _{CC} = 4.5 V to 5.5 V								
		nCP0 inputs	-	45	162	-	202.5	-	220.5	µA
		nCP1, nMR inputs	-	60	216	-	270	-	294	µA
C _I	input capacitance		-	3.5	-	-	-	-	-	pF

10. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			−40 °C to +85 °C		−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
74HC390										
t _{pd}	propagation delay	nCP0 to nQ0; see Figure 5 ^[2]								
		V _{CC} = 2.0 V	-	47	145	-	180	-	220	ns
		V _{CC} = 4.5 V	-	17	29	-	36	-	44	ns
		V _{CC} = 5 V; C _L = 15 pF	-	14	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	25	-	31	-	38	ns
		nCP1 to nQ1; see Figure 5								
		V _{CC} = 2.0 V	-	50	155	-	195	-	235	ns
		V _{CC} = 4.5 V	-	18	31	-	39	-	47	ns
		V _{CC} = 5 V; C _L = 15 pF	-	15	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	26	-	33	-	40	ns
		nCP1 to nQ2; see Figure 5								
		V _{CC} = 2.0 V	-	74	210	-	265	-	315	ns
		V _{CC} = 4.5 V	-	27	42	-	53	-	63	ns
		V _{CC} = 5 V; C _L = 15 pF	-	23	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	22	36	-	45	-	54	ns
		nCP1 to nQ3; see Figure 5								
		V _{CC} = 2.0 V	-	50	155	-	195	-	235	ns
		V _{CC} = 4.5 V	-	18	31	-	39	-	47	ns
		V _{CC} = 5 V; C _L = 15 pF	-	15	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	14	26	-	33	-	40	ns
t _{PHL}	HIGH to LOW propagation delay	nMR to nQn; see Figure 6								
		V _{CC} = 2.0 V	-	52	165	-	205	-	250	ns
		V _{CC} = 4.5 V	-	19	33	-	41	-	50	ns
		V _{CC} = 5 V; C _L = 15 pF	-	16	-	-	-	-	-	ns
		V _{CC} = 6.0 V	-	15	28	-	35	-	43	ns
t _t	transition time	nQn; see Figure 5 ^[3]								
		V _{CC} = 2.0 V	-	19	75	-	95	-	110	ns
		V _{CC} = 4.5 V	-	7	15	-	19	-	22	ns
		V _{CC} = 6.0 V	-	6	13	-	16	-	19	ns

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
t_w	pulse width	nCP0, nCP1; HIGH or LOW; see Figure 5								
		$V_{CC} = 2.0$ V	80	19	-	100	-	120	-	ns
		$V_{CC} = 4.5$ V	16	7	-	20	-	24	-	ns
		$V_{CC} = 6.0$ V	14	6	-	17	-	20	-	ns
		nMR HIGH; see Figure 6								
		$V_{CC} = 2.0$ V	80	28	-	105	-	130	-	ns
		$V_{CC} = 4.5$ V	17	10	-	21	-	26	-	ns
		$V_{CC} = 6.0$ V	14	8	-	18	-	22	-	ns
t_{rec}	recovery time	nMR to nCPn; see Figure 6								
		$V_{CC} = 2.0$ V	75	22	-	95	-	110	-	ns
		$V_{CC} = 4.5$ V	15	8	-	19	-	22	-	ns
		$V_{CC} = 6.0$ V	13	6	-	16	-	19	-	ns
f_{max}	maximum frequency	nCPn; see Figure 5								
		$V_{CC} = 2.0$ V	6.0	20	-	4.8	-	4.0	-	MHz
		$V_{CC} = 4.5$ V	30	60	-	24	-	20	-	MHz
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	66	-	-	-	-	-	MHz
		$V_{CC} = 6.0$ V	35	71	-	28	-	24	-	MHz
C_{PD}	power dissipation capacitance	$C_L = 50$ pF; $f = 1$ MHz; $V_I = \text{GND to } V_{CC}$ ^[4]	-	20	-	-	-	-	-	pF

74HCT390

t_{pd}	propagation delay	nCP0 to nQ0; see Figure 5 ^[2]								
		$V_{CC} = 4.5$ V	-	21	34	-	43	-	51	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	18	-	-	-	-	-	ns
		nCP1 to nQ1; see Figure 5								
		$V_{CC} = 4.5$ V	-	22	38	-	48	-	57	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	19	-	-	-	-	-	ns
		nCP1 to nQ2; see Figure 5								
		$V_{CC} = 4.5$ V	-	30	51	-	64	-	77	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	26	-	-	-	-	-	ns
		nCP1 to nQ3; see Figure 5								
t_{PHL}	HIGH to LOW propagation delay	nMR to nQn; see Figure 6								
		$V_{CC} = 4.5$ V	-	21	36	-	45	-	54	ns
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	18	-	-	-	-	-	ns
t_t	transition time	nQn; see Figure 5 ^[3]								
		$V_{CC} = 4.5$ V	-	7	15	-	19	-	22	ns

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit, see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			–40 °C to +85 °C		–40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	Min	Max	
t_W	pulse width	nCP0, nCP1; HIGH or LOW; see Figure 5								
		$V_{CC} = 4.5$ V	18	8	-	23	-	27	-	ns
		nMR HIGH; see Figure 6								
		$V_{CC} = 4.5$ V	17	10	-	21	-	26	-	ns
t_{rec}	recovery time	nMR to nCPn; see Figure 6								
		$V_{CC} = 4.5$ V	15	8	-	19	-	22	-	ns
f_{max}	maximum frequency	nCPn; see Figure 5								
		$V_{CC} = 4.5$ V	27	55	-	22	-	18	-	MHz
		$V_{CC} = 5$ V; $C_L = 15$ pF	-	61	-	-	-	-	-	MHz
C_{PD}	power dissipation capacitance	$C_L = 50$ pF; $f = 1$ MHz; $V_I = \text{GND to } V_{CC} - 1.5$ V ^[4]	-	21	-	-	-	-	-	pF

[1] All typical values are measured at $T_{amb} = 25$ °C.

[2] t_{pd} is the same as t_{PLH} and t_{PHL} .

[3] t_t is the same as t_{THL} and t_{TLH} .

[4] C_{PD} is used to determine the dynamic power dissipation (P_D in μ W).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

11. Waveforms

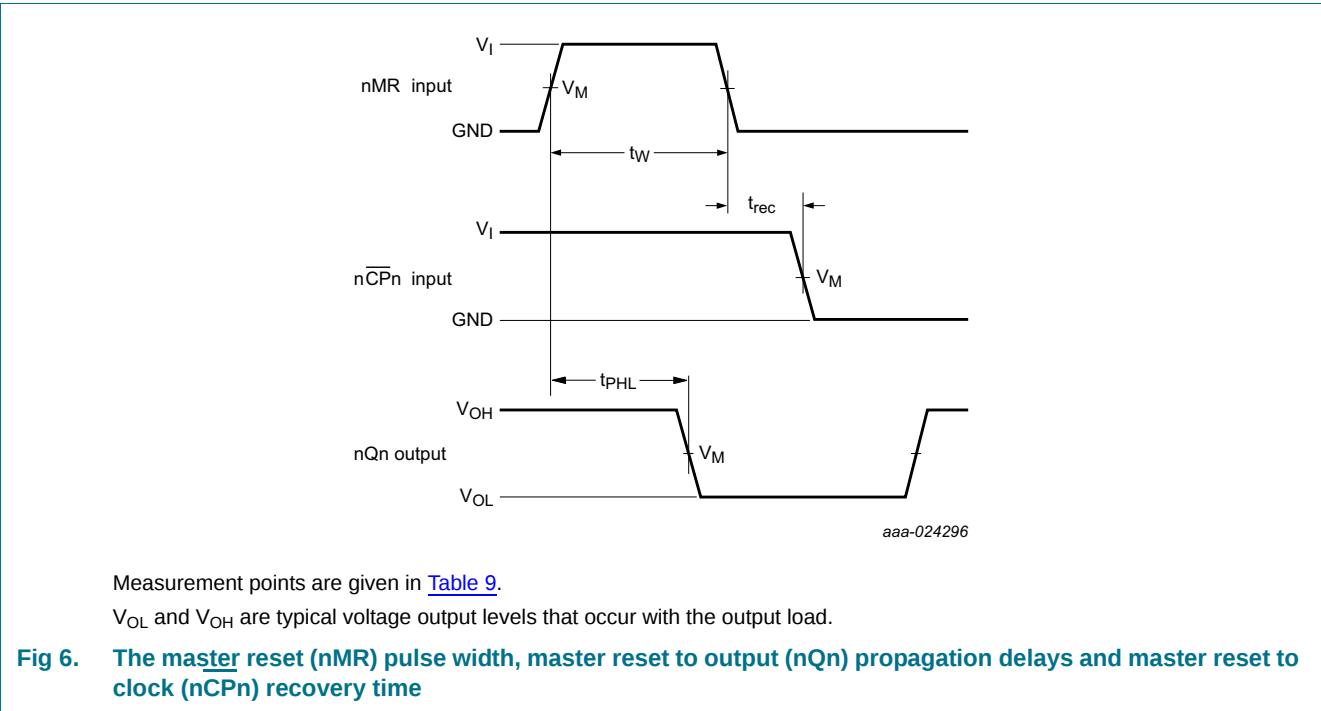
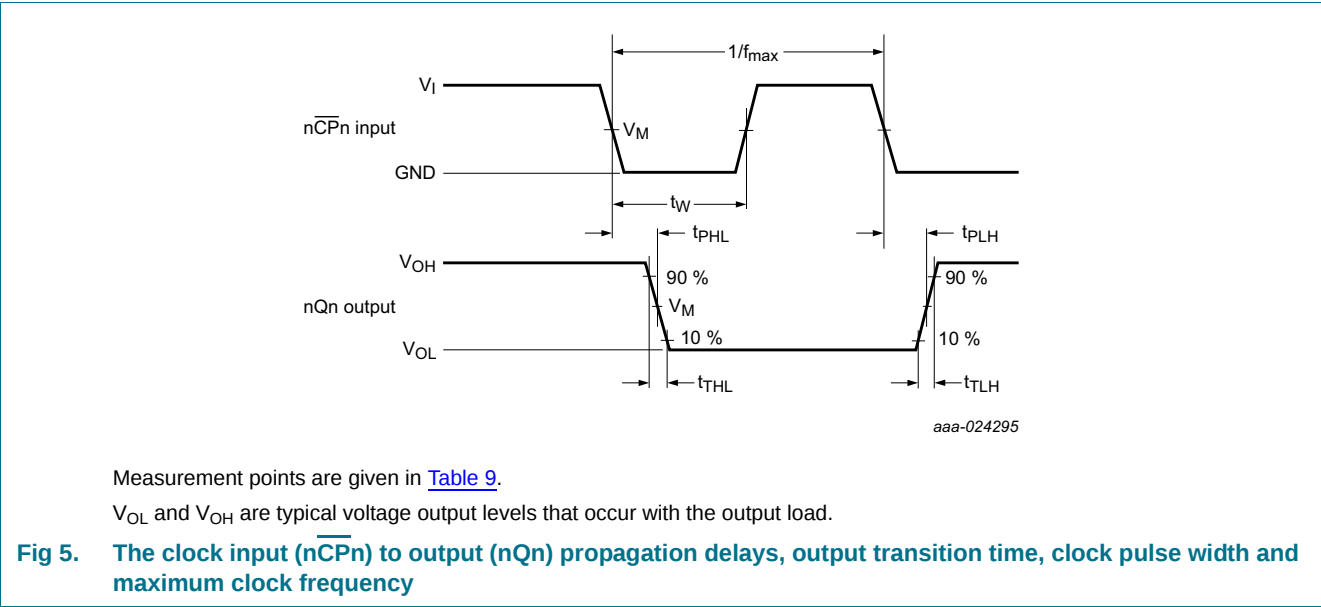
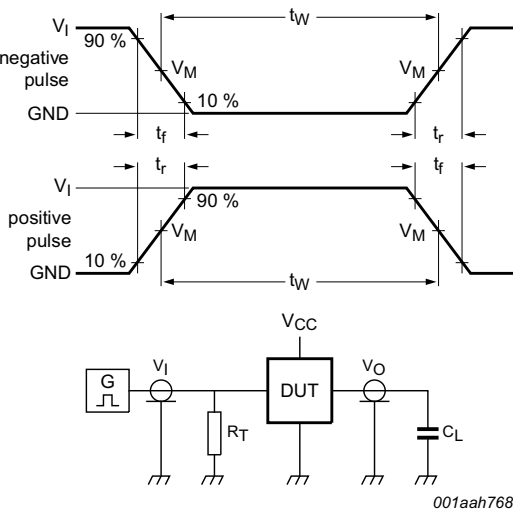


Table 9. Measurement points

Type	Input	Output
	V_M	V_M
74HC390	$0.5V_{CC}$	$0.5V_{CC}$
74HCT390	1.3 V	1.3 V



Test data is given in [Table 10](#).

Definitions test circuit:

R_T = Termination resistance should be equal to output impedance Z_o of the pulse generator.

C_L = Load capacitance including jig and probe capacitance.

Fig 7. Test circuit for measuring switching times

Table 10. Test data

Type	Input		Load	Test
	V_I	t_r, t_f	C_L	
74HC390	V_{CC}	6 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}
74HCT390	3 V	6 ns	15 pF, 50 pF	t_{PLH}, t_{PHL}

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm SOT109-1

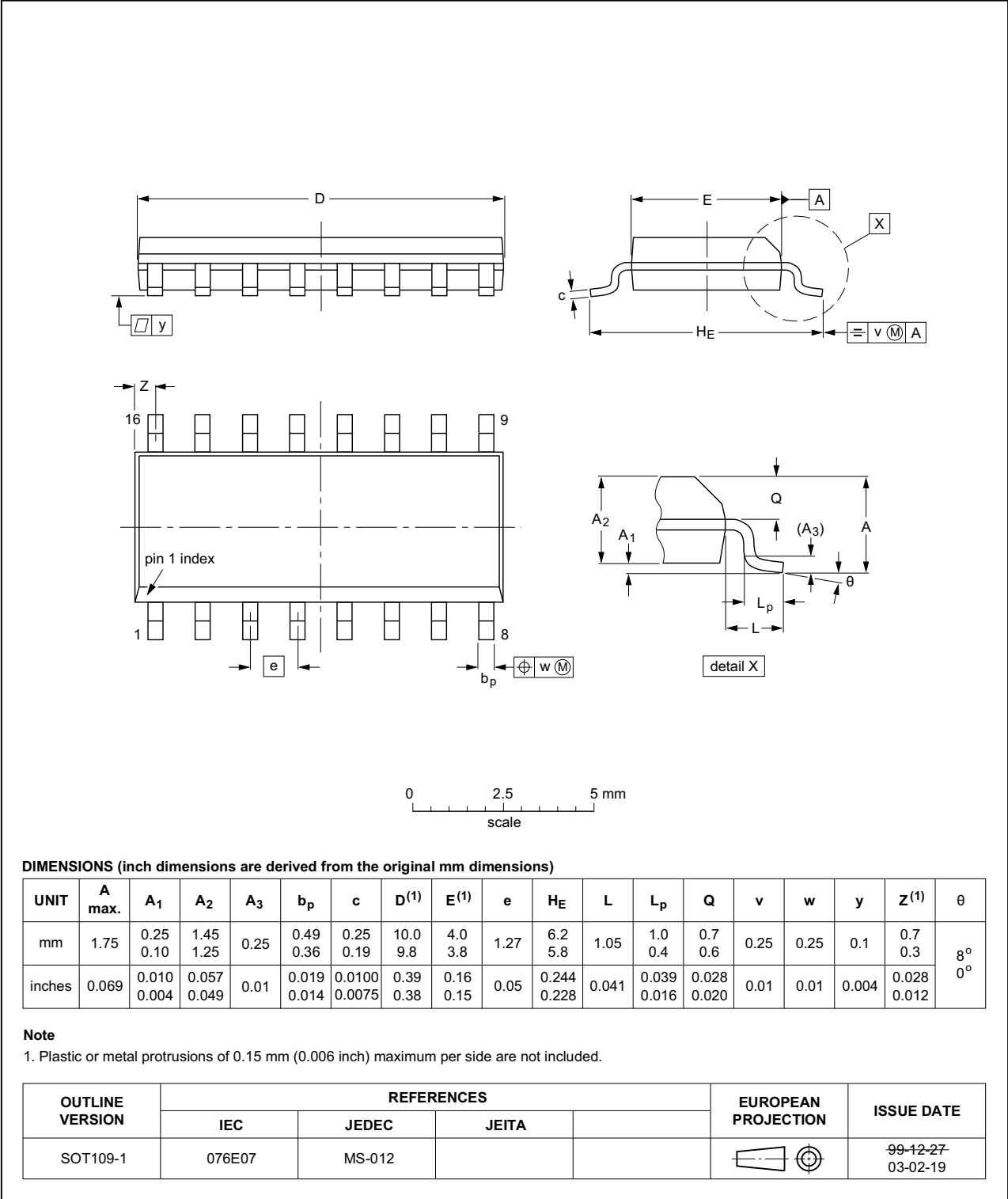


Fig 8. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 5.3 mm

SOT338-1

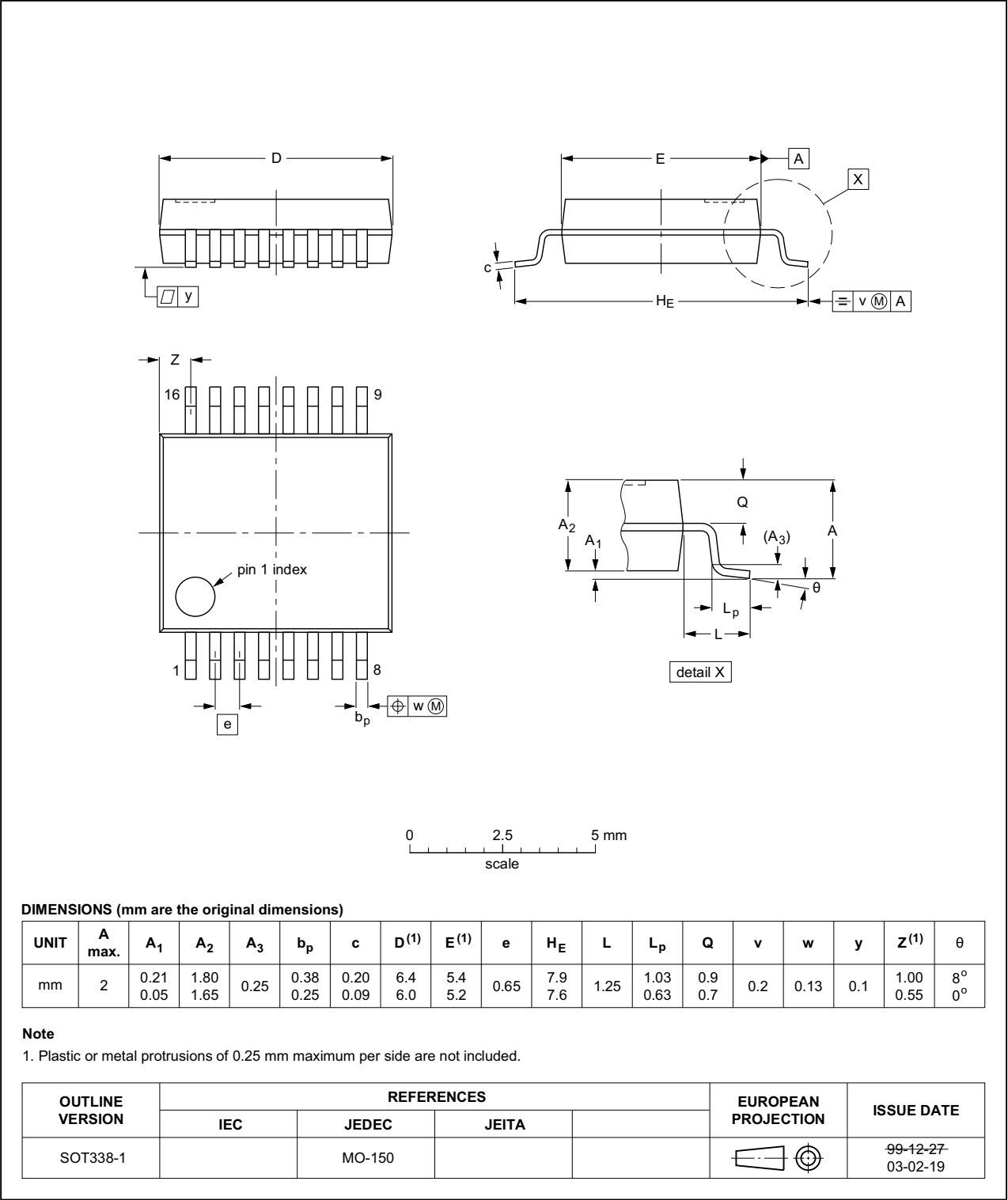


Fig 9. Package outline SOT338-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm

SOT403-1

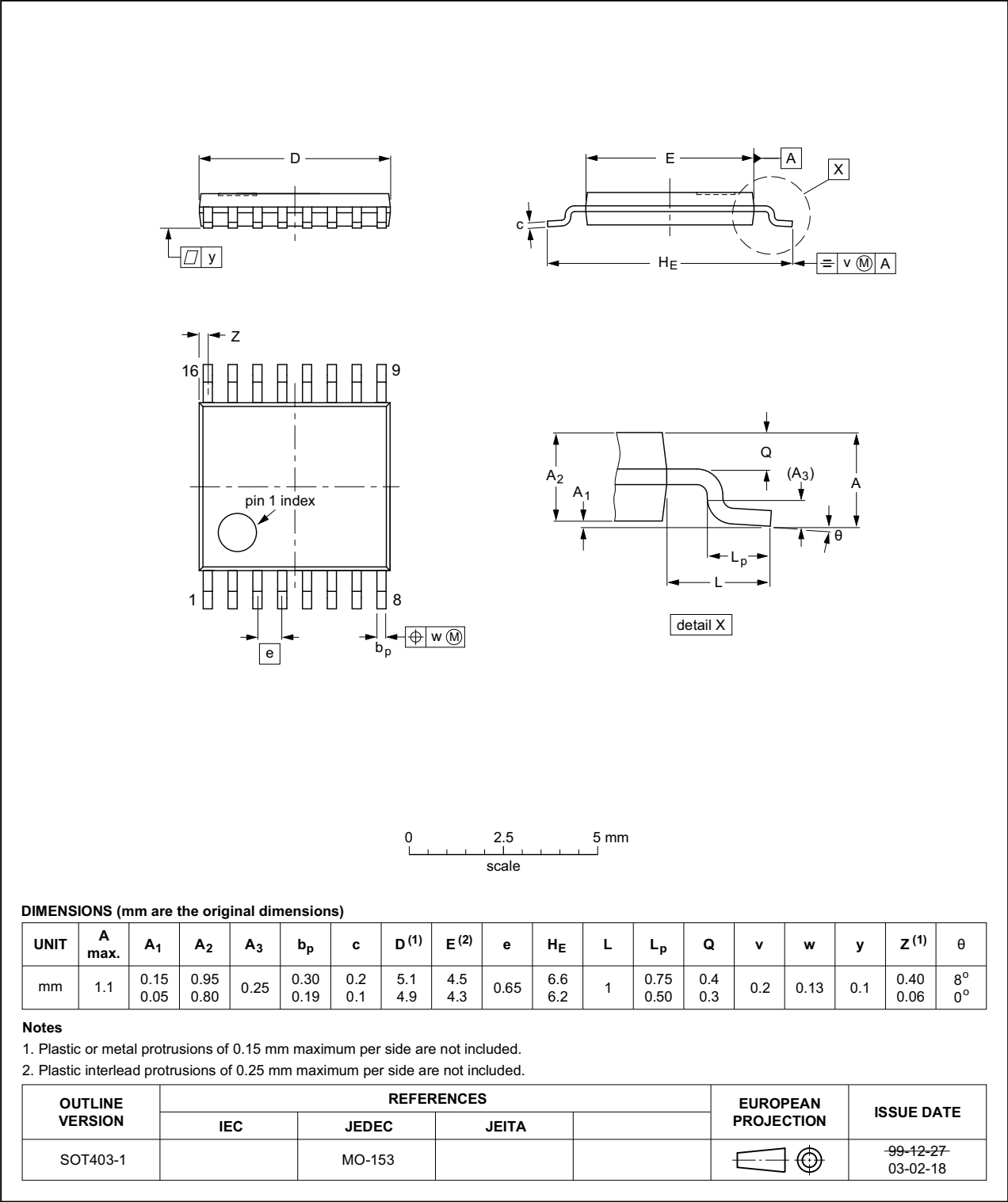


Fig 10. Package outline SOT403-1 (TSSOP16)

13. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT390 v.3	20160816	Product data sheet	-	74HC_HCT390_CNV v.2
Modifications:	- The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors. - Legal texts have been adapted to the new company name where appropriate. - Type numbers 74HC390N and 74HCT390N removed.			
74HC_HCT390_CNV v.2	19901201	Product specification	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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